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DKing  
4-10-02

THE UNITED STATES PATENT & TRADEMARK OFFICE

Application No.: 09/787,661  
Filed: 21 March 2001  
By: Tillack et al.  
For: Method of Fabricating an Amorphous  
or Polycrystalline on an Insulating Region

Examiner: Lattin, C.W.  
Group Art Unit: 2812

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P. O. Box 381516  
Cambridge MA 02238-1516

14 March 2002

Hon.  
Assistant Commissioner for Patents  
Washington DC 20231

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Amendment

Sir:

In response to the Official Letter dated 4 December 2001 (a request for an extension of one month to respond to the Action has been submitted under separate cover), please amend the instant application as follows:

In the Specification:

Page 1, line 8: after "invention" insert --, in general,--;

line 9: after "region" insert --and, more particularly, to a method of

A/

fabricating a semiconductor component with an improved amorphous or polycrystalline silicon germanium layer over an insulating region--;

line 21: correct "size" to --sizes--;